

HIGH-SPEED 8/4K x 18 SYNCHRONOUS PIPELINED DUAL-PORT STATIC RAM

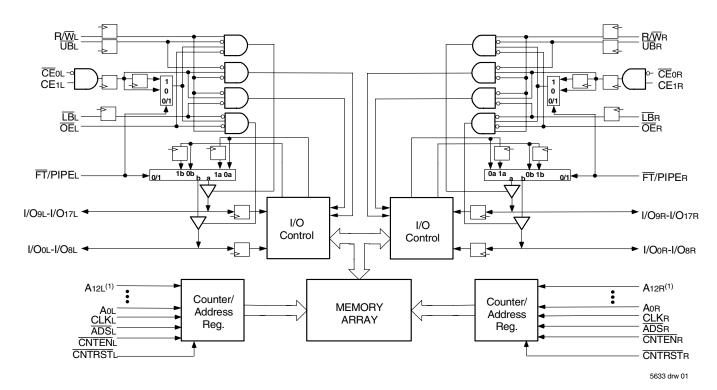
IDT709359/49L

Features

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed clock to data access
 - Commercial: 6.5/7.5/9ns (max.)
 - Industrial: 7.5ns (max.)
- Low-power operation
 - IDT709359/49L Active: 925mW (typ.) Standby: 2.5mW (typ.)
- Flow-Through or Pipelined output mode on either Port via the FT/PIPE pins
- Counter enable and reset features
- Dual chip enables allow for depth expansion without additional logic

- Full synchronous operation on both ports
 - 3.5ns setup to clock and 0ns hold on all control, data, and address inputs
 - Data input, address, and control registers
 - Fast 6.5ns clock to data out in the Pipelined output mode
 - Self-timed write allows fast cycle time
 - 10ns cycle time, 100MHz operation in Pipelined output mode
- Separate upper-byte and lower-byte controls for multiplexed bus and bus matching compatibility
- * TTL- compatible, single 5V (±10%) power supply
- Industrial temperature range (-40°C to +85°C) is available for 83 MHz
- Available in a 100-pin Thin Quad Flatpack (TQFP) package
- Green parts available, see ordering information

Functional Block Diagram



NOTE:

1. A₁₂ is a NC for IDT709349.

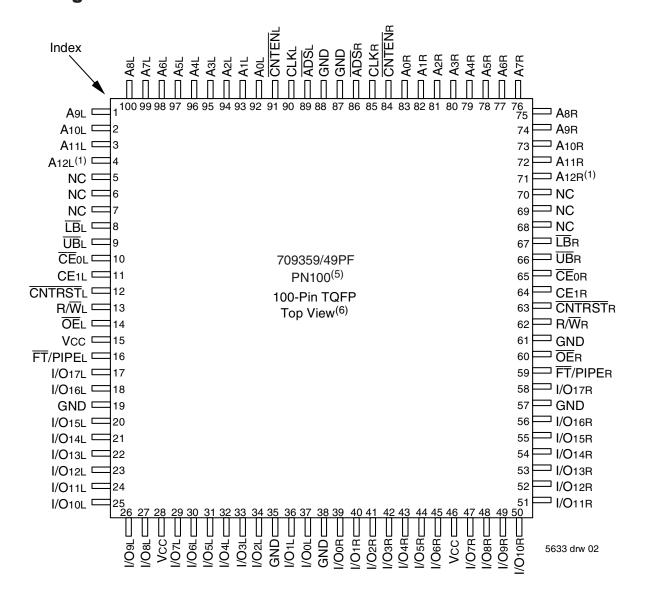
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Description

The IDT709359/49 is a high-speed 8/4K x 18 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times.

With an input data register, the IDT709359/49 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by $\overline{\text{CE}}0$ and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode. Fabricated using CMOS high-performance technology, these devices typically operate on only 925mW of power.

Pin Configurations(1,2,3,4)



- 1. A12 is a NC for IDT709349.
- 2. All Vcc pins must be connected to power supply.
- 3. All GND pins must be connected to ground.
- 4. Package body is approximately 14mm x 14mm x 1.4mm
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

Pin Names

Left Port	Right Port	Names
CEOL, CE1L	CEOR, CE1R	Chip Enables ⁽³⁾
R/WL	R/W̄R	Read/Write Enable
ŌĒL	OE R	Output Enable
A0L - A12L ⁽¹⁾	A0R - A12R ⁽¹⁾	Address
I/O0L - I/O17L	I/O0R - I/O17R	Data Input/Output
CLKL	CLKR	Clock
Ū <u>B</u> L	UB R	Upper Byte Select ⁽²⁾
LB L	LB R	Lower Byte Select ⁽²⁾
ĀDSL	ADS R	Address Strobe
CNTENL	<u>CNTEN</u> R	Counter Enable
CNTRSTL	CNTRSTR	Counter Reset
FT/PIPEL	FT/PIPER	Flow-Through/Pipeline
\	/cc	Power (5V)
	GND	Ground (0V)

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NOTES:

- 1. A₁₂ is a NC for IDT709349.
- 2. $\overline{\text{LB}}$ and $\overline{\text{UB}}$ are single buffered regardless of state of $\overline{\text{FT}}/\text{PIPE}$.
- CEo and CE1 are single buffered when FT/PIPE = VIL, CEo and CE1 are double buffered when FT/PIPE = VIH, i.e. the signals take two cycles to deselect.

Truth Table I—Read/Write and Enable Control^(1,2,3)

ŌĒ	CLK	ՇE₀ ⁽⁵⁾	CE1 ⁽⁵⁾	UB ⁽⁴⁾	LB ⁽⁴⁾	R/W	Upper Byte I/O9-17	Lower Byte I/O ₀₋₈	Mode
Х	↑	Н	Х	Х	Х	Х	High-Z	High-Z	Deselected—Power Down
Х	↑	Х	L	Х	Х	Х	High-Z	High-Z	Deselected—Power Down
Х	↑	L	Н	Η	Н	Х	High-Z	High-Z	Both Bytes Deselected
Х	↑	L	Н	L	Н	L	DATAIN	High-Z	Write to Upper Byte Only
Х	↑	L	Н	Н	L	L	High-Z	DATAIN	Write to Lower Byte Only
Х	↑	L	Н	L	L	L	DATAIN	DATAIN	Write to Both Bytes
L	↑	L	Н	L	Н	Н	DATAout	High-Z	Read Upper Byte Only
L	↑	L	Н	Η	L	Н	High-Z	DATAout	Read Lower Byte Only
L	↑	L	Н	L	L	Н	DATAout	DATAout	Read Both Bytes
Н	Х	L	Н	Х	Х	Х	High-Z	High-Z	Outputs Disabled

NOTES:

- 1. "H" = VIH, "L" = VIL, "X" = Don't Care.
- 2. \overline{ADS} , \overline{CNTEN} , \overline{CNTRST} = X.
- 3. $\overline{\text{OE}}$ is an asynchronous input signa
- 4. $\overline{\text{LB}}$ and $\overline{\text{UB}}$ are single buffered regardless of state of $\overline{\text{FT}}/\text{PIPE}$.
- 5. $\overline{\text{CE}}\text{o}$ and CE1 are single buffered when $\overline{\text{FT}/\text{PIPE}} = V_{\text{IL}}$. $\overline{\text{CE}}\text{o}$ and CE1 are double buffered when $\overline{\text{FT}/\text{PIPE}} = V_{\text{IH}}$, i.e. the signals take two cycles to deselect.

Truth Table II—Address Counter Control^(1,2)

External Address	Previous Internal Address	Internal Address Used	CLK	ĀDS	CNTEN	CNTRST	I/O ⁽³⁾	MODE
An	Х	An	↑	L ⁽⁴⁾	Χ	Н	Dvo (n)	External Address Used
Х	An	An + 1	1	Н	L ⁽⁵⁾	Н	Dvo(n+1)	Counter Enabled—Internal Address generation
Х	An + 1	An + 1	1	Н	Н	Н	Dvo(n+1)	External Address Blocked—Counter disabled (An + 1 reused)
Х	Х	A0	1	Χ	Х	L ⁽⁴⁾	Dvo(0)	Counter Reset to Address 0

NOTES:

5633 tbl 03

- 1. "H" = VIH, "L" = VIL, "X" = Don't Care.
- 2. \overline{CE}_0 , \overline{LB} , \overline{UB} , and \overline{OE} = VIL; CE1 and R/ \overline{W} = VIH.
- 3. Outputs configured in Flow-Through Output mode: if outputs are in Pipelined mode the data out will be delayed by one cycle.
- 4. ADS and CNTRST are independent of all other signals including CE0, CE1, UB and LB.
- The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other signals including CE₀, CE₁, UB and LB.

Recommended Operating Recommen Temperature and Supply Voltage⁽¹⁾ Conditions

Grade	Ambient Temperature ⁽¹⁾	GND	Vcc
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

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NOTES:

- Industrial temperature: for specific speeds, packages and powers contact your sales office.
- 2. This is the parameter TA. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
Vн	Input High Voltage	2.2	_	6.0 ⁽¹⁾	V
VIL	Input Low Voltage	-0.5 ⁽²⁾	_	0.8	V

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NOTES:

- 1. VTERM must not exceed Vcc + 10%.
- 2. $V_{IL} \ge -1.5V$ for pulse width less than 10ns.

Absolute Maximum Ratings(1)

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	٧
TBIAS	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-65 to +150	°C
Іоит	DC Output Current	50	mA

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc + 10%.

Capacitance⁽¹⁾

$(TA = +25^{\circ}C, f = 1.0MHz)$

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
CIN	Input Capacitance	VIN = 3dV	9	pF
Cout ⁽³⁾	Output Capacitance	Vout = 3dV	10	pF

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NOTES:

- 1. These parameters are determined by device characterization, but are not production tested.
- 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.
- 3. Cout also references Ci/o.

DC Electrical Characteristics Over the Operating Temperature Supply Voltage Range (Vcc = 5.0V ± 10%)

				709359/49L		
Symbol	Parameter	Test Conditions	Min.	Max.	Unit	
lu	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, Vin = 0V to Vcc	ı	5	μΑ	
lLO	Output Leakage Current	CE₀ = ViH or CE₁ = ViL, Vouт = 0V to Vcc	_	5	μΑ	
Vol	Output Low Voltage	IoL = +4mA	_	0.4	V	
Vон	Output High Voltage	Iон = -4mA	2.4	_	V	

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NOTE

1. At Vcc ≤ 2.0V input leakages are undefined.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽³⁾ ($Vcc = 5V \pm 10\%$)

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						9/49L6 I Only	709359 Com'l		709359 Com'l		
Symbol	Parameter	Test Condition	Versi	on	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Unit
Icc	Dynamic Operating Current	CEL and CER= VIL	COM'L	L	230	430	210	400	185	360	mA
	(Both Ports Active)	Outputs Disabled f = fMAX ⁽¹⁾	IND	L		_	210	440			1
ISB1	Standby Current (Both Ports - TTL	CEL = CER = VIH	COM'L	L	45	115	40	105	35	95	mA
	Level Inputs)	$f = fMAX^{(1)}$	IND	L		_	40	120			
ISB2	Standby Current (One Port - TTL	CE"A" = VIL and CE"B" = VIH ⁽³⁾ Active Port Outputs Disabled, f=fMAX ⁽¹⁾	COM'L	L	150	235	135	220	120	205	mA
	Level Inputs)		IND	L	_		135	235	_	_	
ISB3	Full Standby Current	Both Ports CER and	COM'L	L	0.5	3.0	0.5	3.0	0.5	3.0	mA
	(Both Ports - CMOS Level Inputs)	$CEL \ge VCC - 0.2V$ $VIN \ge VCC - 0.2V$ or $VIN \le 0.2V$, $f = 0^{(2)}$	IND	L			0.5	3.0	_		
ISB4	Full Standby Current	\overline{CE} "A" $\leq 0.2V$ and	COM'L	L	160	210	130	190	110	170	mA
(One Port - CMOS Level Inputs)		el Inputs) \overline{CE} ''B" \geq Vcc - 0.2V ⁽⁵⁾ $\overline{VIN} \geq$ Vcc - 0.2V or $\overline{VIN} \leq$ 0.2V, Active Port Outputs Disabled, f = fMaX ⁽¹⁾		L	_	_	130	205	_	_	

5633 tbl 09

- At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.
- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. Vcc = 5V, $TA = 25^{\circ}C$ for Typ, and are not production tested. $Icc \, Dc(f=0) = 150 \, \text{mA}$ (Typ).
- 5. CEx = VIL means \overline{CE}_{0x} = VIL and CE1x = VIH
 - CEx = VIH means \overline{CE}_{0x} = VIH or CE1x = VIL
 - CEx \leq 0.2V means $\overline{\text{CE}}_{0x} \leq$ 0.2V and CE1x \geq Vcc 0.2V
 - CEx \geq Vcc 0.2V means $\overline{\text{CE}}_{0x} \geq$ Vcc 0.2V or CE1x \leq 0.2V
 - "X" represents "L" for left port or "R" for right port.

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	2ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1, 2 and 3

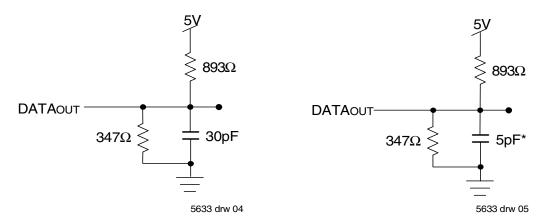


Figure 1. AC Output Test load.

Figure 2. Output Test Load (For tckLz, tckHz, toLz, and toHz). *Including scope and jig.

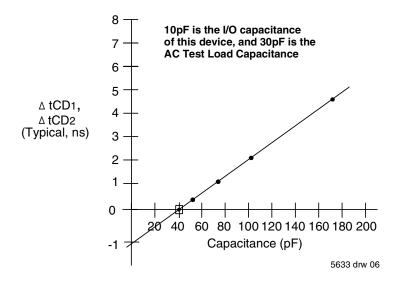


Figure 3. Typical Output Derating (Lumped Capacitive Load).

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing) $^{(3)}$ (Vcc = 5V ± 10%)

	(100		709359/49L6 Com'l Only		9/49L7 & Ind	709359/49L9 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽²⁾	19	_	22	_	25	_	ns
tcyc2	Clock Cycle Time (Pipelined) ⁽²⁾	10	_	12	_	15	_	ns
tcH1	Clock High Time (Flow-Through) ⁽²⁾	6.5	_	7.5		12	_	ns
ta_1	Clock Low Time (Flow-Through)(2)	6.5	_	7.5		12	_	ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	4	_	5		6	_	ns
tal2	Clock Low Time (Pipelined) ⁽²⁾	4	_	5	_	6	_	ns
tr	Clock Rise Time	_	3		3		3	ns
tF	Clock Fall Time	_	3		3		3	ns
tsa	Address Setup Time	3.5		4		4		ns
tha	Address Hold Time	0		0		1		ns
tsc	Chip Enable Setup Time	3.5	_	4		4		ns
thc	Chip Enable Hold Time	0		0		1		ns
tsB	Byte Enable Setup Time	3.5	_	4		4		ns
tнв	Byte Enable Hold Time	0	_	0		1		ns
tsw	R/W Setup Time	3.5	_	4		4		ns
thw	R/W Hold Time	0		0		1		ns
tsp	Input Data Setup Time	3.5	_	4	_	4	_	ns
tHD	Input Data Hold Time	0	_	0	_	1	_	ns
tsad	ADS Setup Time	3.5		4		4		ns
thad	ADS Hold Time	0		0		1		ns
tscn	CNTEN Setup Time	3.5		4		4		ns
thon	CNTEN Hold Time	0		0		1		ns
tsrst	CNTRST Setup Time	3.5	_	4		4	_	ns
thrst	CNTRST Hold Time	0	_	0	_	1	_	ns
toE	Output Enable to Data Valid		6.5	_	7.5	_	9	ns
toLz	Output Enable to Output Low-Z ⁽¹⁾	2	_	2	_	2	_	ns
tonz	Output Enable to Output High-Z ⁽¹⁾	1	7	1	7	1	7	ns
tCD1	Clock to Data Valid (Flow-Through)(2)	_	15		18	_	20	ns
tCD2	Clock to Data Valid (Pipelined) ⁽²⁾	_	6.5		7.5	_	9	ns
toc	Data Output Hold After Clock High	2	_	2		2	_	ns
tckHZ	Clock High to Output High-Z ⁽¹⁾	2	9	2	9	2	9	ns
tcĸLz	Clock High to Output Low-Z ⁽¹⁾	2	_	2		2	_	ns
Port-to-Port D	lelay	,					•	
tcwdd	Write Port Clock High to Read Data Delay	_	24		28		35	ns
tocs	Clock-to-Clock Setup Time	_	9		10	_	15	ns
		-					-	

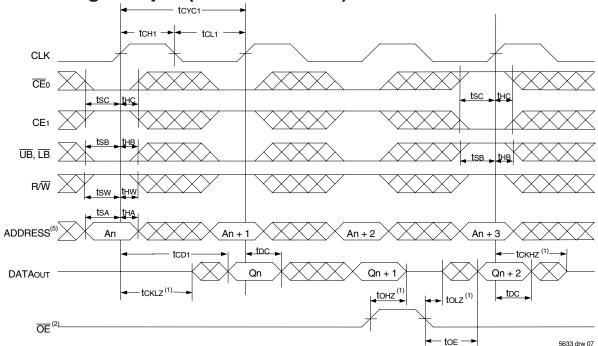
NOTES:

^{1.} Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2). This parameter is guaranteed by device characterization, but is not production tested.

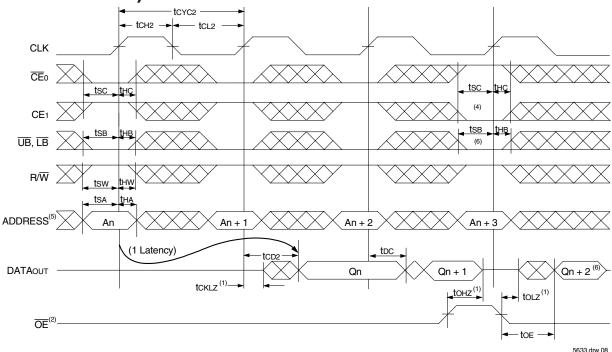
^{2.} The Pipelined output parameters (tcyc2, tcD2) to either the Left or Right ports when FT/PIPE = VIH. Flow-Through parameters (tcyc1, tcD1) apply when FT/PIPE = VIL for that port.

^{3.} All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE), FT/PIPER and FT/PIPEL.

Timing Waveform of Read Cycle for Flow-Through Output (FT/PIPE"x" = VIL)(3,7)

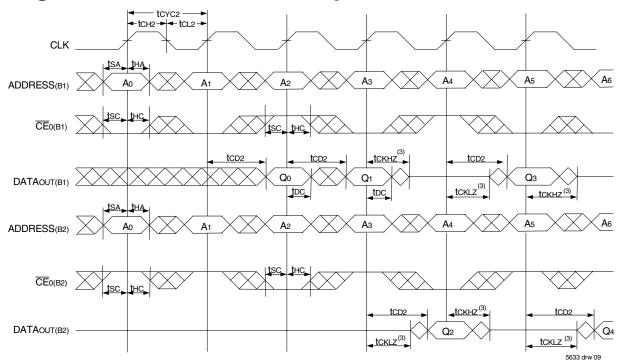


Timing Waveform of Read Cycle for Pipelined Operation $(\overline{FT}/PIPE"x" = Vih)^{(3,7)}$

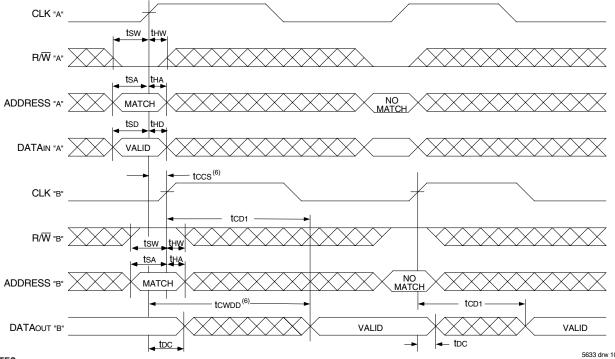


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. \overline{OE} is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 3. $\overline{ADS} = VIL, \overline{CNTEN}$ and $\overline{CNTRST} = VIH.$
- 4. The output is disabled (High-Impedance state) by $\overline{\text{CE}}_0 = \text{V}_{\text{IH}}$, CE1 = VIL, following the next rising edge of the clock. Refer to Truth Table 1.
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers
 are for reference use only.
- 6. If $\overline{\sf UB}$ or $\overline{\sf LB}$ was HIGH, then the Upper Byte and/or Lower Byte of DATAouT for Qn + 2 would be disabled (High-Impedance state).
- 7. "X" here denotes Left or Right port. The diagram is with respect to that port.

Timing Waveform of a Bank Select Pipelined Read^(1,2)



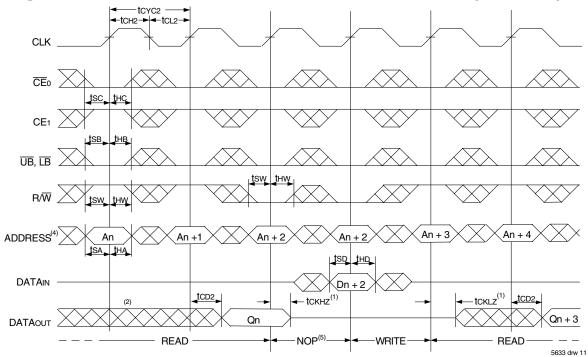
Timing Waveform of Write with Port-to-Port Flow-Through Read (4,5,7)



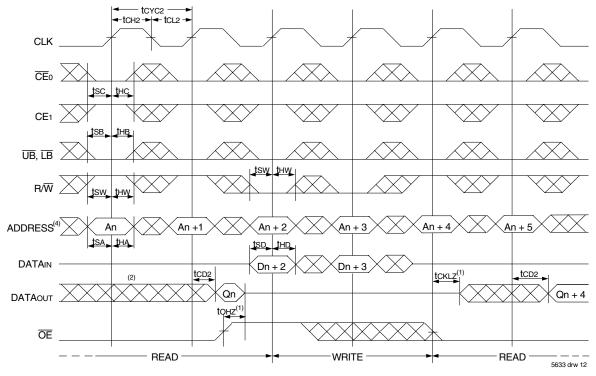
- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT709359/49 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. $\overline{\text{UB}}$, $\overline{\text{LB}}$, $\overline{\text{OE}}$, and $\overline{\text{ADS}}$ = VIL; CE1(B1), CE1(B2), R/W, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}}$ = VIH.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. \overline{CE}_0 , \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; CE1, \overline{CNTEN} , and \overline{CNTRST} = VIH.
- 5. $\overline{OE} = V_{\parallel}$ for the Right Port, which is being read from. $\overline{OE} = V_{\parallel}$ for the Left Port, which is being written to.
- If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwdd.

 If tccs > maximum specified, then data from right port READ is not valid until tccs + tcdl. tcwdd does not apply in this case.
- 7. All timing is the same for both Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite from Port "A".

Timing Waveform of Pipelined Read-to-Write-to-Read (OE = VIL)(3)

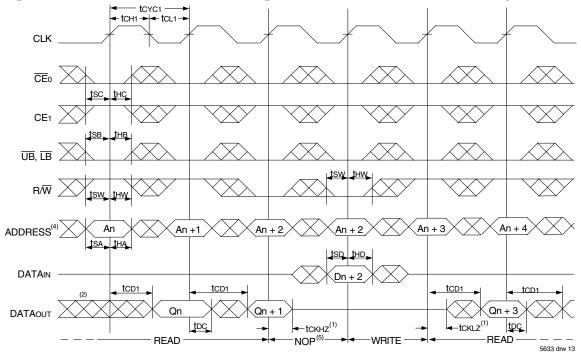


Timing Waveform of Pipelined Read-to-Write-to-Read (OE Controlled)(3)

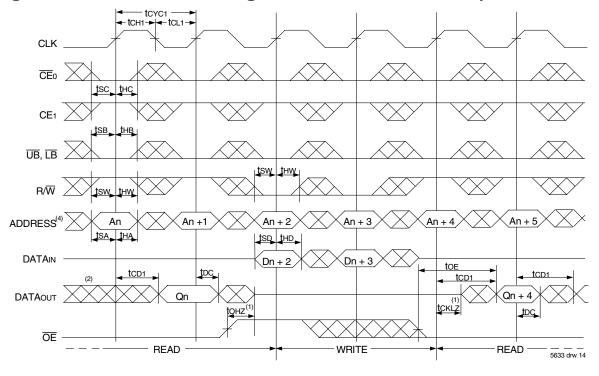


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- B. CEO, UB, LB, and ADS = VIL; CE1, CNTEN, and CNTRST = VIH. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since $\overline{ADS} = V_{IL}$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Flow-Through Read-to-Write-to-Read ($\overline{\text{OE}}$ = V_IL)⁽³⁾

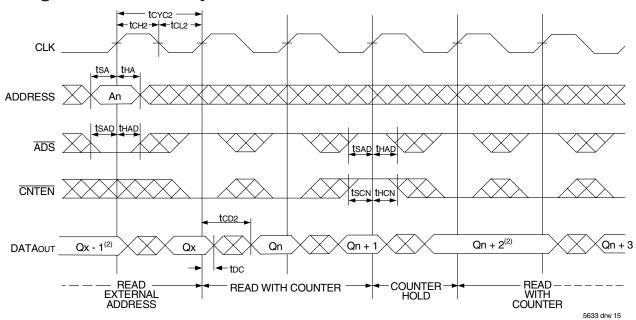


Timing Waveform of Flow-Through Read-to-Write-to-Read (OE Controlled)(3)

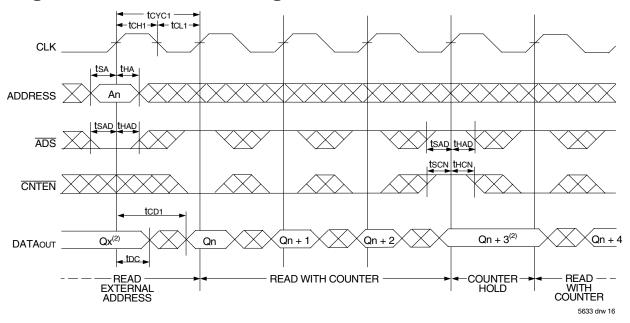


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance is determined by the previous cycle control signals.
- 3. \overline{CE}_0 , \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; \overline{CE}_1 , \overline{CNTEN} , and \overline{CNTRST} = VIH. "NOP" is "No Operation".
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾

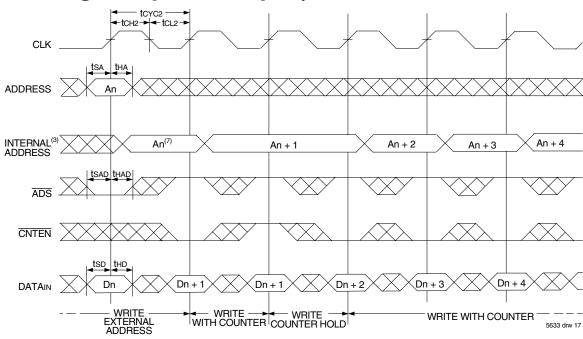


Timing Waveform of Flow-Through Read with Address Counter Advance⁽¹⁾

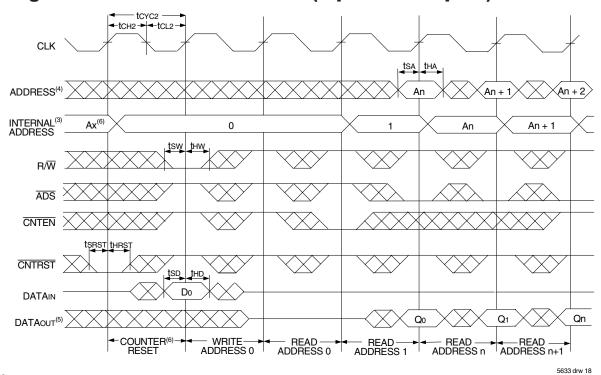


- 1. \overline{CE}_0 , \overline{OE} , \overline{UB} , and \overline{LB} = VIL; CE1, R/ \overline{W} , and \overline{CNTRST} = VIH.
- 2. If there is no address change via $\overline{ADS} = VIL$ (loading a new address) or $\overline{CNTEN} = VIL$ (advancing the address), i.e. $\overline{ADS} = VIH$ and $\overline{CNTEN} = VIH$, then the data output remains constant for subsequent clocks.

Timing Waveform of Write with Address Counter Advance (Flow-Through or Pipelined Outputs)⁽¹⁾



Timing Waveform of Counter Reset (Pipelined Outputs)(2)



- 1. $\overline{CE_0}$, \overline{UB} , \overline{LB} , and $R/\overline{W} = V_{IL}$; CE_1 and $\overline{CNTRST} = V_{IH}$.
- 2. \overline{CE}_0 , \overline{UB} , \overline{LB} = VIL, CE1 = VIH.
- 3. The "Internal Address" is equal to the "External Address" when ADS = VIL and equals the counter output when ADS = VIH.
- 4. Addresses do not have to be accessed sequentially since ADS = VI∟ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset cycle.
- 7. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1' Address is written to during this cycle.

A Functional Description

The IDT709359/49 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

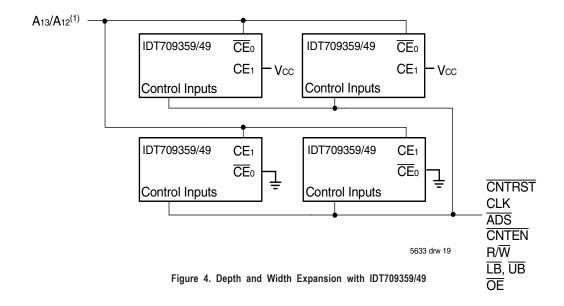
An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

 $\overline{\text{CE}}_0$ = VIH or CE1 = VIL for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT709359/49's for depth expansion configurations. When the Pipelined output mode is enabled, two cycles are required with $\overline{\text{CE}}_0$ = VIL and CE1 = VIH to re-activate the outputs.

Depth and Width Expansion

The IDT709359/49 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

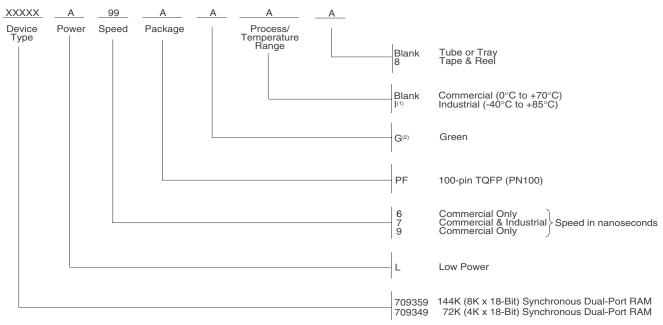
The IDT709359/49 can also be used in applications requiring expanded width, as indicated in Figure 4. Since the banks are allocated at the discretion of the user, the external controller can be set up to drive the input signals for the various devices as required to allow for 36-bit or wider applications.



NOTE:

1. A13 is for IDT709359, A12 is for IDT709349

Ordering Information



5633 drw 2

NOTE:

- 1. Contact your local sales office for industrial temp range for other speeds, packages and powers.
- 2. Green parts available. For specific speeds, packages and powers contact your sales office.

Datasheet Document History

07/08/02: Initial Public Release 08/18/03: Removed Preliminary status

Page 16 Added IDT Clock Solution Table

10/21/08: Page16 Removed "IDT" from orderable part number

05/21/15: Page 1 Added green availability to Features

Page 1 Removed 100-pin fine pitch Ball Grid Array fpBGA offering from Features

Page 2 Removed IDT in reference to fabrication

Page 3 The package code PN100-1 changed to PN100 to match standard package codes

Page 3 Removed the date for the PN100-pin TQFP configuration

Page 4 Removed the 100-pin fine pitch Ball Grid Array fpBGA configuration and corresponding footnotes

Page 5 Corrected typo in footnote text

Page 7 Corrected typo in the Typical Output Derating drawing

Page 8 Removed the commercial temp range from the AC Elec Chars Read & Write Cycle Timing table title Page 15 Added Tape & Reel and Green indicators with their footnote annotations to the Ordering Information

Page 15 Removed the 100-pin TQFP fpBGA from the Ordering Information

Page 15 Removed IDT Clock table



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